# N-Channel 30-V (D-S) MOSFET

## **Key Features:**

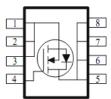
- Low r<sub>DS(on)</sub> trench technology
- · Low thermal impedance
- Fast switching speed

### **Typical Applications:**

- White LED boost converters
- Automotive Systems
- Industrial DC/DC Conversion Circuits

PRODUCT SUMMARY				
Vds (V)	$r_{DS(on)}(m\Omega)$	I⊳(A)		
30	10 @ V <sub>GS</sub> = 10V	16		
	13 @ V <sub>GS</sub> = 4.5V	14		





ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^{\circ}C$ UNLESS OTHERWISE NOTED)							
Parameter		Symbol	Limit	Units			
Drain-Source Voltage	V <sub>DS</sub>	30	V				
Gate-Source Voltage	V <sub>GS</sub>	±20	v				
Continuous Drain Current <sup>a</sup>	T <sub>A</sub> =25°C	I_	16	A			
	T <sub>A</sub> =70°C	I <sub>D</sub>	12				
Pulsed Drain Current <sup>b</sup>		I <sub>DM</sub>	50				
Continuous Source Current (Diode Conduction) <sup>a</sup>		I <sub>S</sub>	5.1	А			
Power Dissipation <sup>a</sup>	T <sub>A</sub> =25°C	P <sub>D</sub>	3.5	W			
	T <sub>A</sub> =70°C	١D	2	vv			
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	-55 to 150	°C			

THERMAL RESISTANCE RATINGS						
Parameter			Maximum	Units		
Maximum Junction-to-Ambient <sup>a</sup>	t <= 10 sec	D	35	°C/W		
	Steady State	R <sub>θJA</sub>	81	C/W		

Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

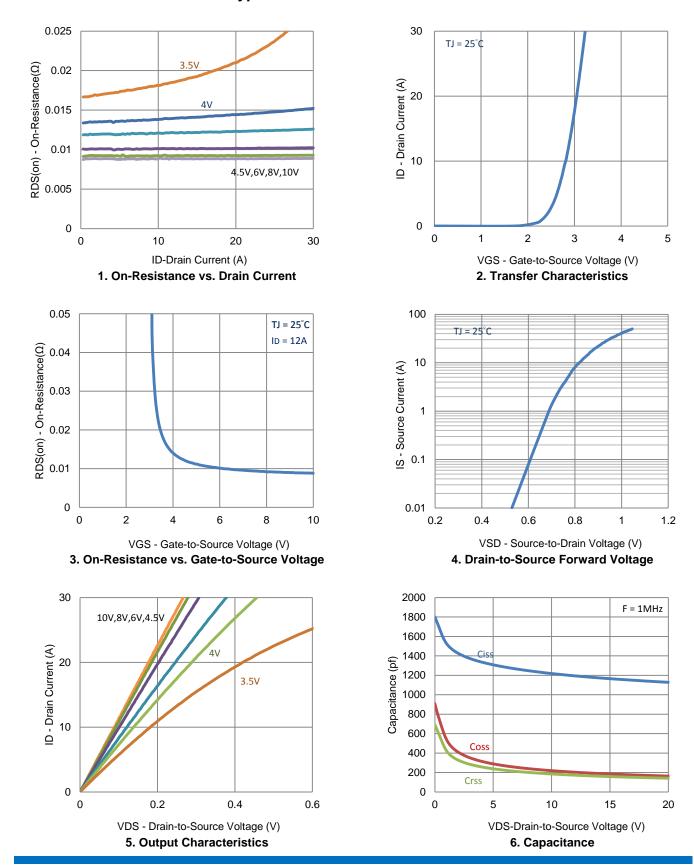
## **Electrical Characteristics**

Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Static							
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_D = 250 \text{ uA}$				V	
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V},  V_{GS} = \pm 20 \text{ V}$			±100	nA	
Zara Cata Valtaga Drain Current		$V_{DS} = 24 \text{ V}, V_{GS} = 0 \text{ V}$			1	uA	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{DS} = 24 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			25	uA	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} = 5 V, V_{GS} = 10 V$	25			А	
Drain-Source On-Resistance <sup>a</sup>	r	$V_{GS} = 10 \text{ V}, \text{ I}_{D} = 12 \text{ A}$			10	mΩ	
Drain-Source On-Resistance	r <sub>DS(on)</sub>	$V_{GS} = 4.5 \text{ V}, \text{ I}_{D} = 9.6 \text{ A}$			13	11152	
Forward Transconductance <sup>a</sup>	<b>g</b> <sub>fs</sub>	$V_{DS} = 15 \text{ V}, \text{ I}_{D} = 12 \text{ A}$		25		S	
Diode Forward Voltage <sup>a</sup>	$V_{SD}$	$I_{S} = 2.6 \text{ A}, V_{GS} = 0 \text{ V}$		0.74		V	
		Dynamic <sup>b</sup>					
Total Gate Charge	$Q_{g}$	V <sub>DS</sub> = 15 V, V <sub>GS</sub> = 4.5 V,		12		nC	
Gate-Source Charge	$Q_gs$	$V_{DS} = 13 V, V_{GS} = 4.5 V,$ $I_{D} = 12 A$		4.7			
Gate-Drain Charge	$Q_gd$	10 - 1277		5.1			
Turn-On Delay Time	t <sub>d(on)</sub>			6			
Rise Time	t <sub>r</sub>	$V_{DS}$ = 15 V, $R_L$ = 1.3 $\Omega$ , $I_D$ = 12 A,		15		ns	
Turn-Off Delay Time	t <sub>d(off)</sub>	$V_{GEN}$ = 10 V, $R_{GEN}$ = 6 $\Omega$		38			
Fall Time	t <sub>f</sub>			20			
Input Capacitance	C <sub>iss</sub>			1165			
Output Capacitance	C <sub>oss</sub>	$V_{DS}$ = 15 V, $V_{GS}$ = 0 V, f = 1 MHz		185		pF	
Reverse Transfer Capacitance	C <sub>rss</sub>	][		158			

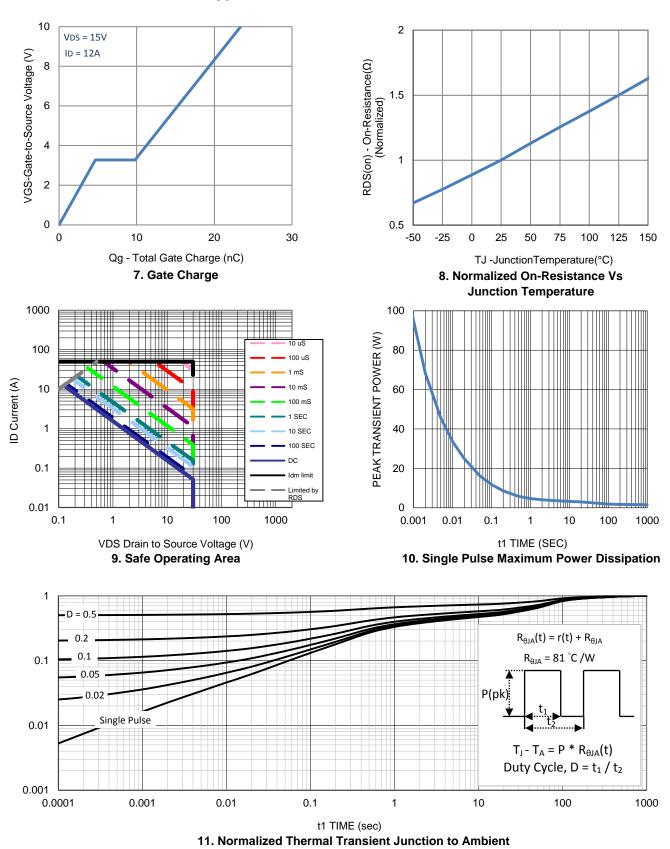
#### Notes

- a. Pulse test: PW <= 300us duty cycle <= 2%.
- b. Guaranteed by design, not subject to production testing.

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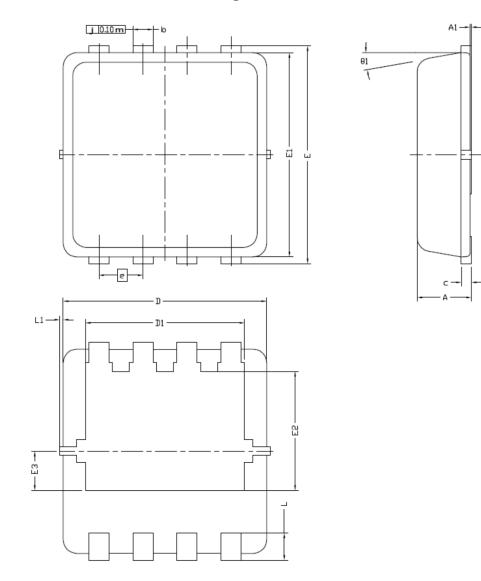


### **Typical Electrical Characteristics**



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## Package Information



птм	MILLIMETERS			INCHES			
DIM,	MIN	NDM	MAX	MIN	NDM	MAX	
Α	0,700	0,80	0,900	0,0276	0.0315	0,0354	
A1	0,00		0,05	0.000		0'005	
b	0.24	0.30	0.35	0.009	0.012	0.014	
С	0.10	0.152	0.25	0.004	0.006	0.010	
D	3.00 BSC			0.118 BSC			
D1	2.35 BSC			0.093 BSC			
E	3.20 BSC			0.126 BSC			
E1	3	3.00 BSC			0.118 BSC		
E5	1.75 BSC			0.069 BSC			
E3	0,575 BSC			0.023 BSC			
е	0.65 BSC			0.026 BSC			
L	0,30	0,40	0,50	0,0118	0.0157	0.0197	
L1	0		0,100	0		0,004	
81	0°	10°	12°	0*	10*	12°	

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